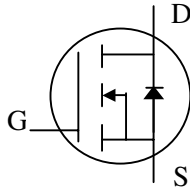




N-channel Enhancement-mode Power MOSFET

- Simple Drive Requirement**
- Fast Switching Characteristics**
- Low Gate Charge**
- RoHS-compliant, halogen-free**



BV_{DSS}	120V
$R_{DS(ON)}$	185mΩ
I_D	8.8A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP9997AGH-HF-3 is in the TO-252 package which is widely preferred for commercial and industrial surface mount applications such as medium-power DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	±20	V
I_D at $T_C=25\text{ }^\circ\text{C}$	Continuous Drain Current ³	8.8	A
I_D at $T_C=100\text{ }^\circ\text{C}$	Continuous Drain Current ³	5.6	A
I_{DM}	Pulsed Drain Current ¹	30	A
P_D at $T_C=25\text{ }^\circ\text{C}$	Total Power Dissipation	34.7	W
	Linear Derating Factor	0.28	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	3.6	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	°C/W

Ordering Information

AP9997AGH-HF-3TR RoHS-compliant, halogen-free TO-252 shipped on tape and reel (3000 pcs/reel)



Electrical Specifications at $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	120	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	-	-	185	m Ω
		$V_{GS}=6V, I_D=5A$	-	-	225	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.8	-	2.5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=8A$	-	8	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=96V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=8A$	-	15	24	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=96V$	-	2.7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	6.7	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=60V$	-	5.5	-	ns
t_r	Rise Time	$I_D=8A$	-	13.5	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	16	-	ns
t_f	Fall Time	$R_D=7.5\Omega$	-	4	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	550	880	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	55	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	40	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=8A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=8A, V_{GS}=0V$	-	60	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	150	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.
 USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.
 APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED
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 APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE
 RELIABILITY, FUNCTION OR DESIGN.



Typical Electrical Characteristics

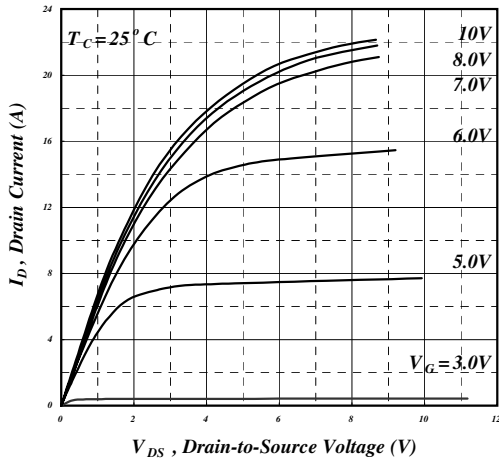


Fig 1. Typical Output Characteristics

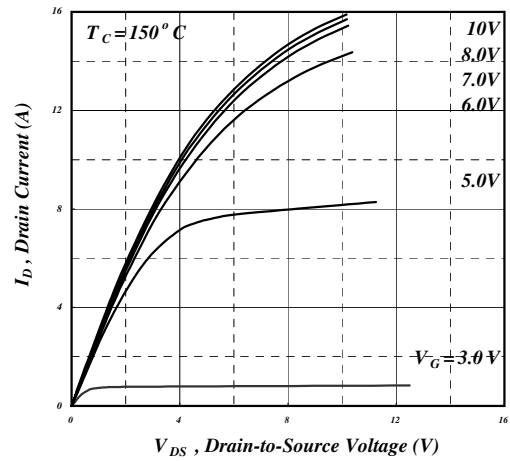


Fig 2. Typical Output Characteristics

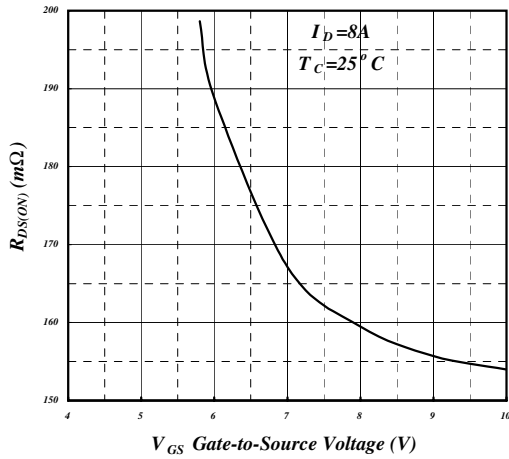


Fig 3. On-Resistance vs. Gate Voltage

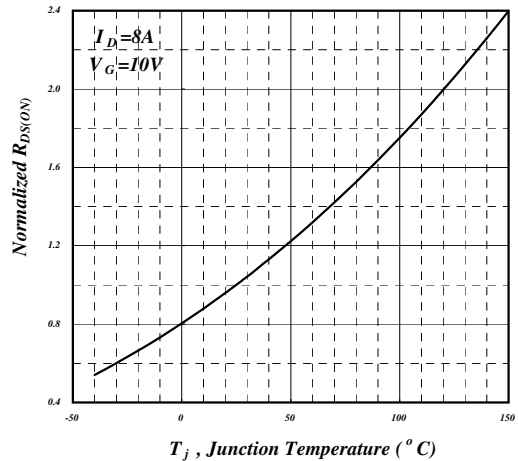


Fig 4. Normalized On-Resistance vs. Junction Temperature

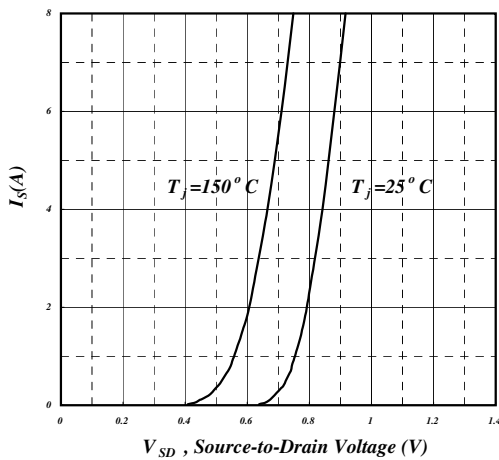


Fig 5. Forward Characteristic of Reverse Diode

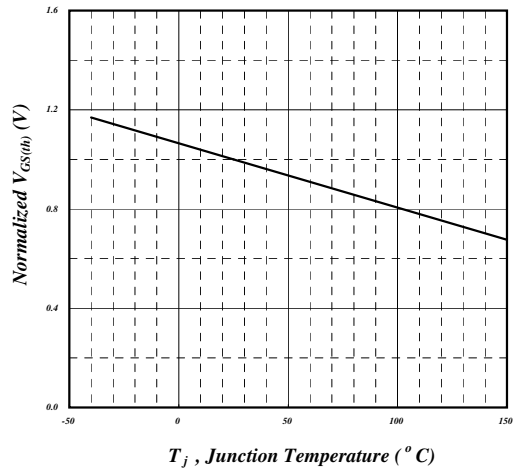


Fig 6. Gate Threshold Voltage vs. Junction Temperature



Typical Electrical Characteristics (cont.)

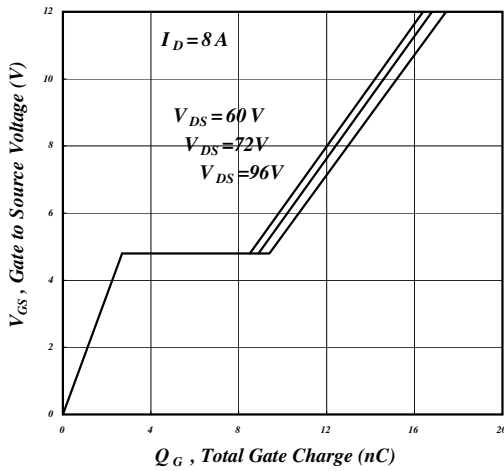


Fig 7. Gate Charge Characteristics

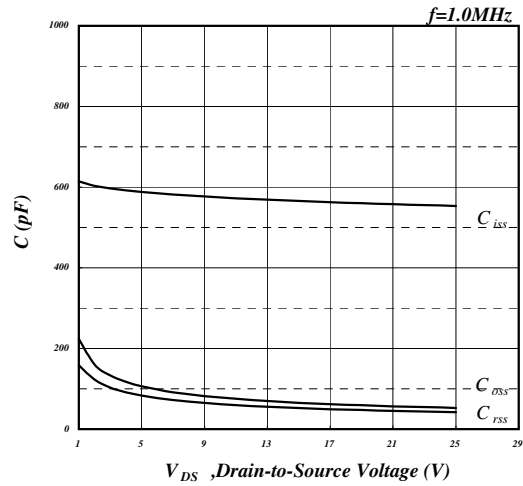


Fig 8. Typical Capacitance Characteristics

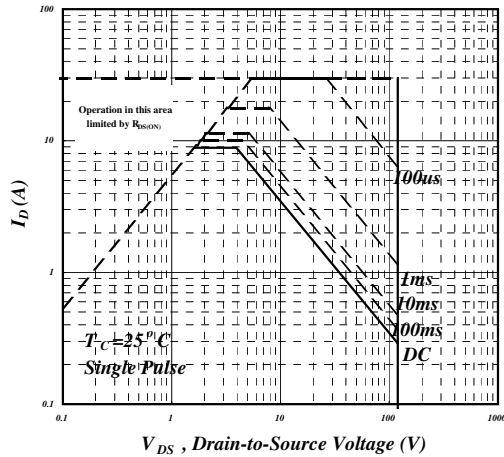


Fig 9. Maximum Safe Operating Area

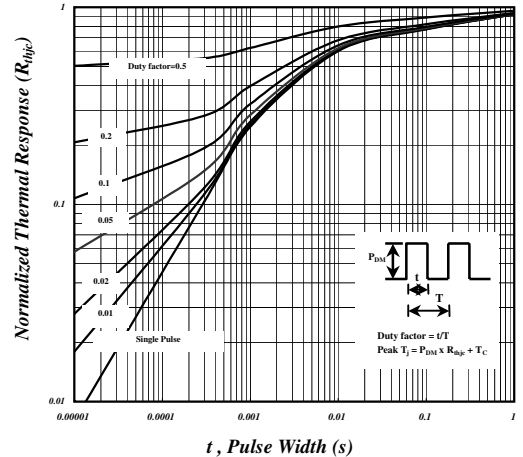


Fig 10. Effective Transient Thermal Impedance

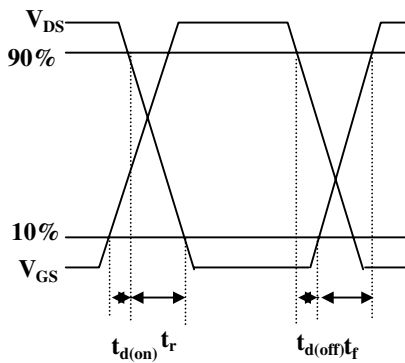


Fig 11. Switching Time Waveforms

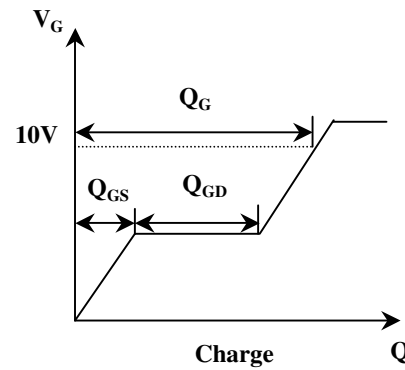
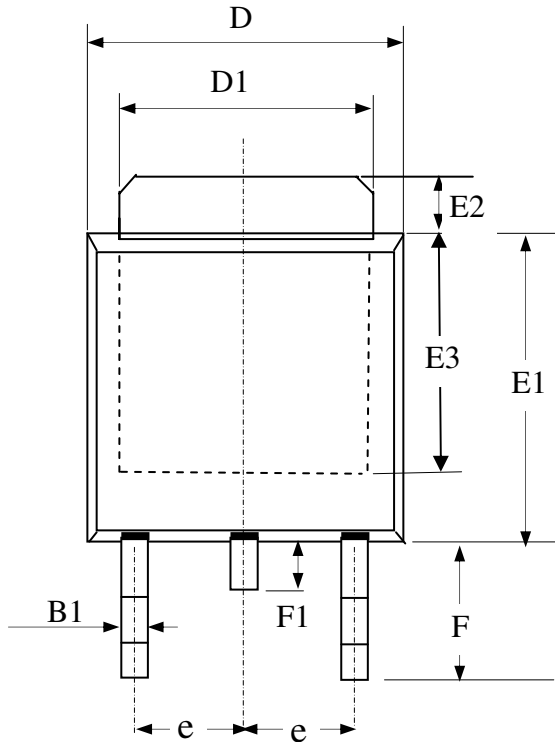


Fig 12. Gate Charge Waveform

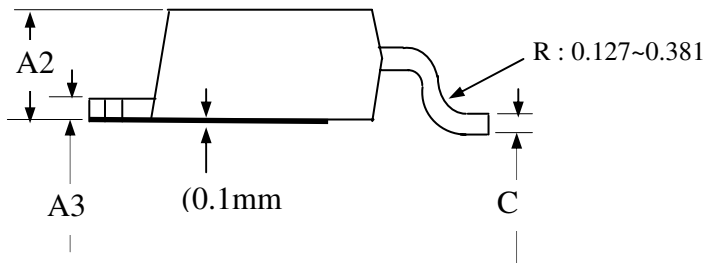


Package Dimensions: TO-252



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.



Marking Information: TO-252

Laser Marking

